

Drafts Pending Active

- L1: (11026) floating.clm. and control.clm.
- L2: (1845) 1 and dielectric.clm.
- L3: (1777) 2 and gate.clm.
- L4: (402) 3 and annealing
- L5: (242) 4 and (etchS3.clm. or patternS3.clm.)
- L6: (243) 5 and (memory or (non adj volatile))
- L7: (213) 6 and polysilicon
- L8: (205) 7 and (control adj gate).clm.
- L9: (204) 8 and (floating adj gate).clm.
- L10: (72) 9 and annealS3.clm.
- L11: (68) 10 and silicon
- L12: (6) 11 and (silicon near7 (chamber or vacuum or (in adj situ)))
- L13: (64) 10 and ((polysilicon or silicon) near10 (dopS3 or vapor))
- L14: (41) 10 and ((polysilicon or silicon) near10 (dopS3 or vapor)).clm.
- L15: (?) 14 and ((polysilicon or silicon) near3 ((in adj situ) or chamber or

 Failed Saved

- (0) ("thinadjfilm)nearresistor").PN.
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Document ID	Issue Date	Paged	Title	Current OR	Current	Examiner	Att.	C.	P.	F.	U.
US 200301237	20030123	7	Method of manufacturing	438/257	257/E21.20	Lueh, Tuung et al.					
US 20030017670			a semiconductor memory		9						
US 20020028541	20020307	151	Dense arrays and charge	438/149	257/E21.02	Lee, Thomas H. et al.					
US 6746893	20040608	28	storage devices and ma		6						
US 6380029	20020430	15	Transistor with variable electron affin	438/105	438/257	Forbes, Leonard et al.					
US 6380029	20020430	15	Method of forming ono	438/257	257/E21.20	Cheng, Kent Kuohua et al.					
US 6316316	20011113	9	Stacked films and DCS t		9						
US 6228718	20010508	16	Method of forming high density and low power f	438/260	257/E21.01	Wu, Shye-Lin					
US 6117756	20000912	9	Method of fabricating a self-aligned split gate	438/266	257/E21.68	Huang, Chih-Jen et al.					
			density and low power f		2						
					257/E21.01						

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